

1.Description

The IRF540N uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

3.Features

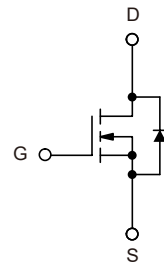
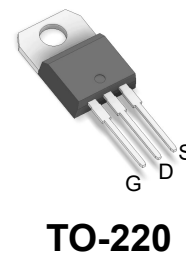
- $V_{DS}=100V$, $I_D=30A$
- $R_{DS(ON)}<40m\Omega$ @ $V_{GS}=10V$
- High density cell design for lower R_{dson}

2.Application

- Power switching application
- Hard switched and High frequency circuits
- Uninterruptible power supply

4.Pinning information

Pin	Symbol	Description
1	G	GATE
2	D	DRAIN
3	S	SOURCE



5.Absolute Maximum Ratings $T_A=25^{\circ}C$

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	30	A
Drain Current-Pulsed (Note 1)	I_{DM}	100	A
Maximum Power Dissipation ($T_C=25^{\circ}C$)	P_D	70	W
Single pulse avalanche energy (Note 2)	E_{AS}	96	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	$^{\circ}C$



6.Thermal Characteristic

Parameter	Symbol	Limit	Units
Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	3.5	°C/W



7. Electrical Characteristics ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _{DS} =250μA	100			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V			1	μA
Gate-Body Leakage	I _{GSS}	V _{GS} =±20V, V _{DS} =0V			±100	nA
On Characteristic						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2	3	2.5	V
Drain-Source On-State Resistance ^(Note 3)	R _{DS(ON)}	V _{GS} =10V, I _D =12A		40	44	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =15A		22		S
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1MHz		2550		pF
Output Capacitance	C _{oss}			225		pF
Reverse Transfer Capacitance	C _{rss}			205		pF
Switching Characteristics						
Turn-On Delay Time	t _{D(on)}	V _{DD} =50V, I _D =20A R _{GEN} =10Ω, V _{GS} =10V		29		nS
Rise Time	t _r			13		nS
Turn-Off Delay Time	t _{D(off)}			58.2		nS
Fall Time	t _f			13.4		nS
Total Gate Charge	Q _g	V _{DS} =80V, I _D =20A, V _{GS} =10V		55		nC
Gate-Source Charge	Q _{gs}			15		nC
Gate-Drain Charge	Q _{gd}			20		nC



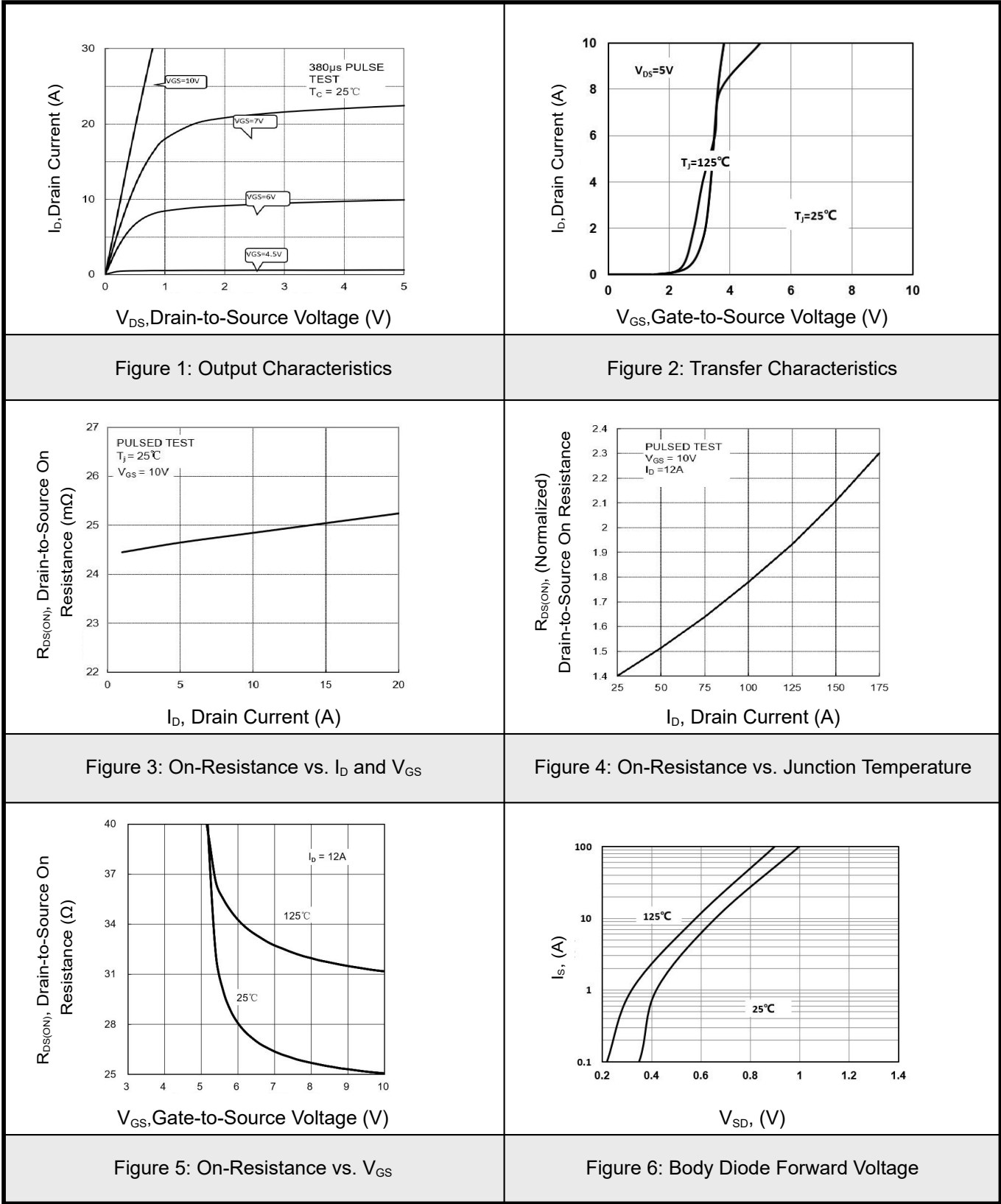
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=20A$			1.2	V
Reverse Recovery Time	t_{rr}	$T_J=25^{\circ}C, I_F=10A$		58		nS
Reverse Recovery Charge	Q_{rr}	$di/dt=100A/\mu s$ (Notes 3)		110		nC

Notes:

- 1: Repetitive rating, pulse width limited by maximum junction temperature.
- 2: E_{AS} condition : $T_J=25^{\circ}C, V_{DD}=50V, V_{GS}=10V, L=0.5mH, R_g=25\Omega$.
- 3: Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
- 4: Guaranteed by design, not subject to production.



8.1 Typical Characteristics





8.2 Typical Characteristics

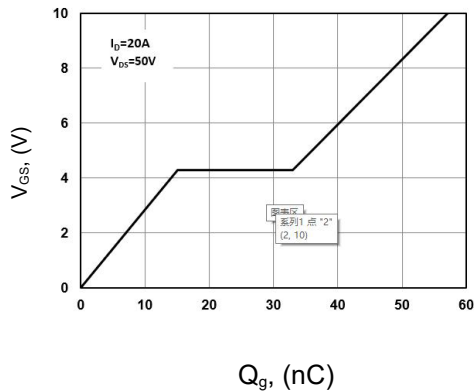


Figure 7: Gate-Charge Characteristics

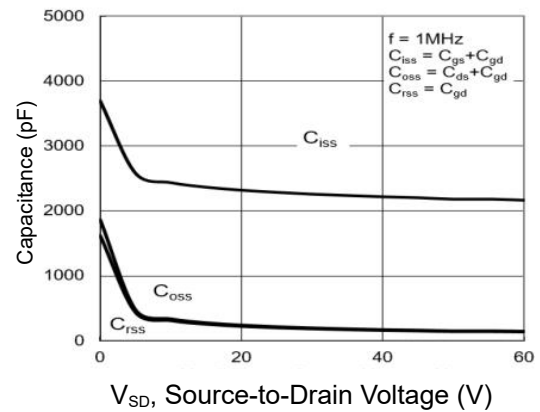


Figure 8: Source-Drain Diode Forward Voltage

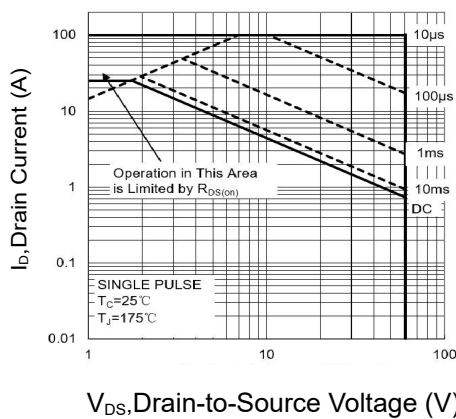


Figure 9: Maximum Forward Biased Safe Operation Area

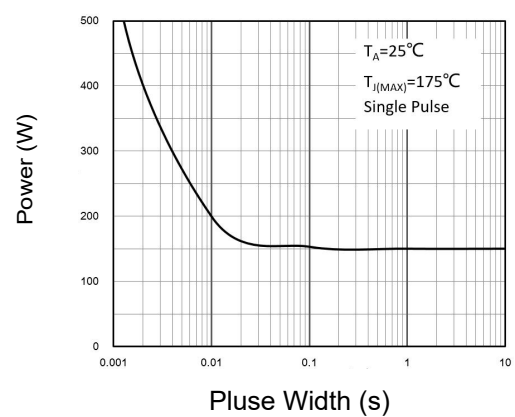


Figure 10: Single Pulse Power Rating Junction-to-Ambient

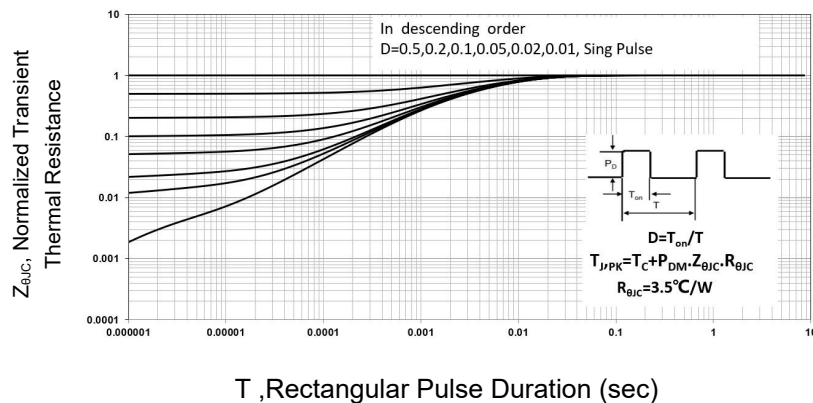
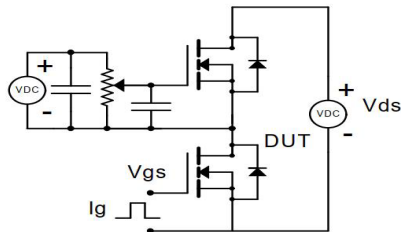


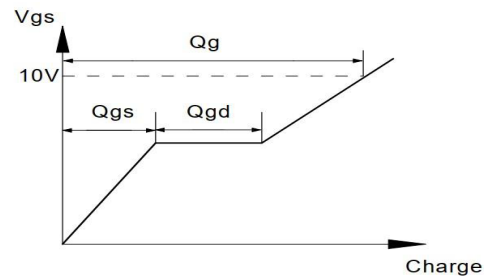
Figure 11: Normalized Maximum Transient Thermal Impedance



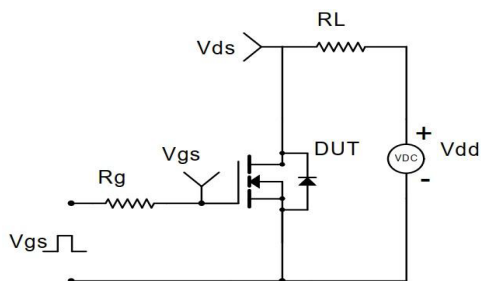
8.3 Typical Characteristics



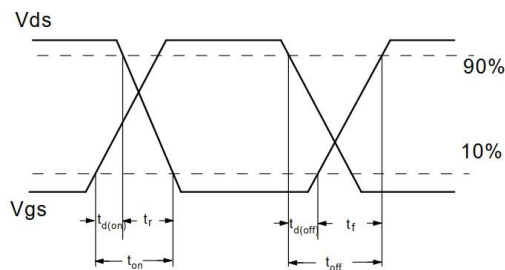
Gate Charge Test Circuit



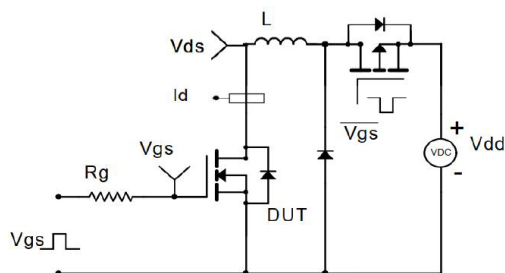
Gate Charge Test Waveform



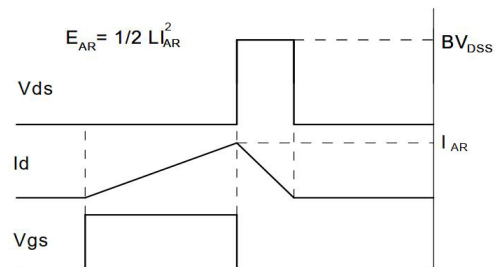
Resistive Switching Test Circuit



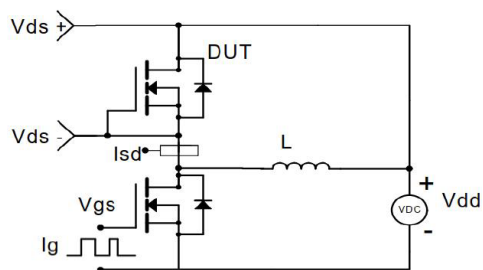
Resistive Switching Test Waveforms



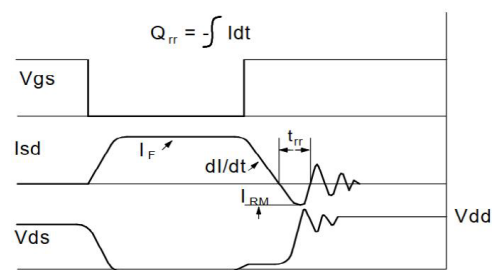
Unclamped Inductive Switching (UIS) Test Circuit



Unclamped Inductive Switching (UIS) Test Waveforms



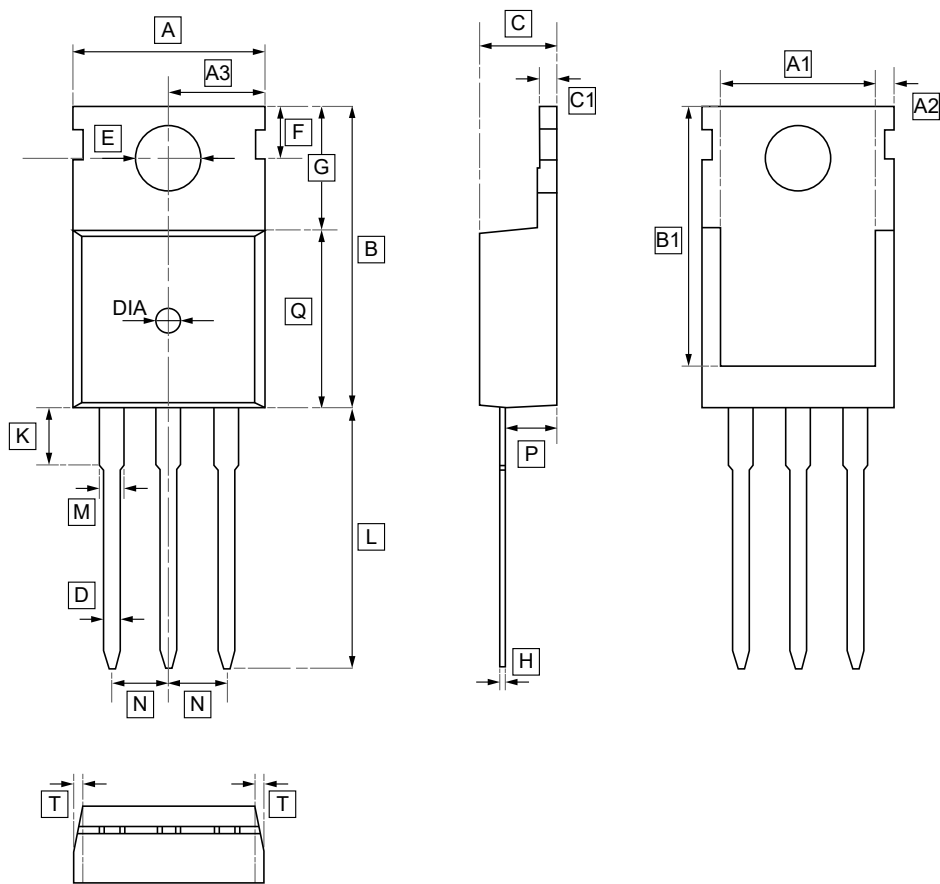
Diode Recovery Test Circuit



Diode Recovery Test Waveforms



9.1 TO-220 Package Outline Dimensions



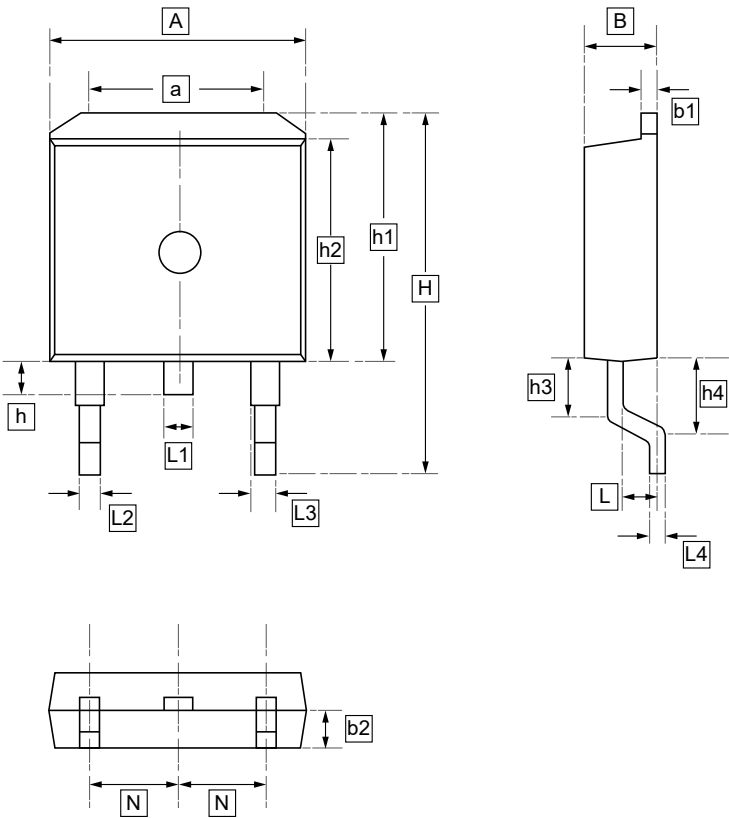
DIMENSIONS (mm are the original dimensions)

Symbol	A	A1	A2	A3	B	B1	C	C1	D	E	F	G
Min	9.7	8.44	1.05	4.8	15.4	12.9	4.28	1.1	0.6	3.4	2.65	5.2
Max	10.3	8.84	1.25	5.2	16.2	13.5	4.68	1.5	1.0	3.8	3.25	5.8

Symbol	H	K	L	L1	M	N	P	Q	T	DIA
Min	0.4	2.9	12.8	2.7	1.15	2.49	2.1	8.7	W:0.35	⌀1.5
Max	0.6	3.3	13.6	3.3	1.35	2.59	2.7	9.3		(deep 0.2)



9.2 TO-263 Package Outline Dimensions



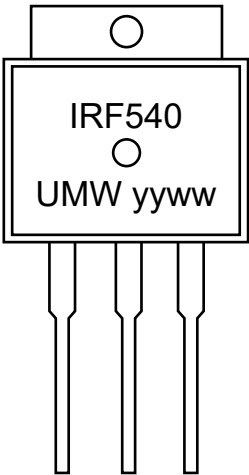
DIMENSIONS (mm are the original dimensions)

Symbol	A	a	B	b1	b2	H	h	h1	h2	h3	h4	L	L1	L2	L3
Min	9.6	7.2	4.3	1.25	2.2	15.2	1.34	10.3	9.1	1.34	2.5	2.2	1.2	0.7	1.2
Max	10.0	7.6	4.7	1.35	2.6	15.8	1.74	10.7	9.3	1.74	2.9	2.6	1.4	0.9	1.4

Symbol	L4	N
Min	0.4	2.4
Max	0.6	2.5



10.Ordering information



yy: Year Code
ww: Week Code

Order Code	Marking	Package	Base QTY	Delivery Mode
UMW IRF540N	IRF540	TO-220	1000	Tape and reel
UMW IRF540NSTRL	F540NS	TO-263	800	Tape and box



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